

PN4249

FAIRCHILD SEMICONDUCTOR TM

PN4249



PNP General Purpose Amplifier

This device is designed for use as general purpose amplifiers and switches requiring collector currents to 300 mA. Sourced from Process 68. See PN200 for characteristics.

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CEO}	Collector-Emitter Voltage	60	V
Vсво	Collector-Base Voltage	60	V
V _{EBO}	Emitter-Base Voltage	5.0	V
lc	Collector Current - Continuous	500	mA
TJ, Tstg	Operating and Storage Junction Temperature Range	-55 to +150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics

TA = 25°C unless otherwise noted

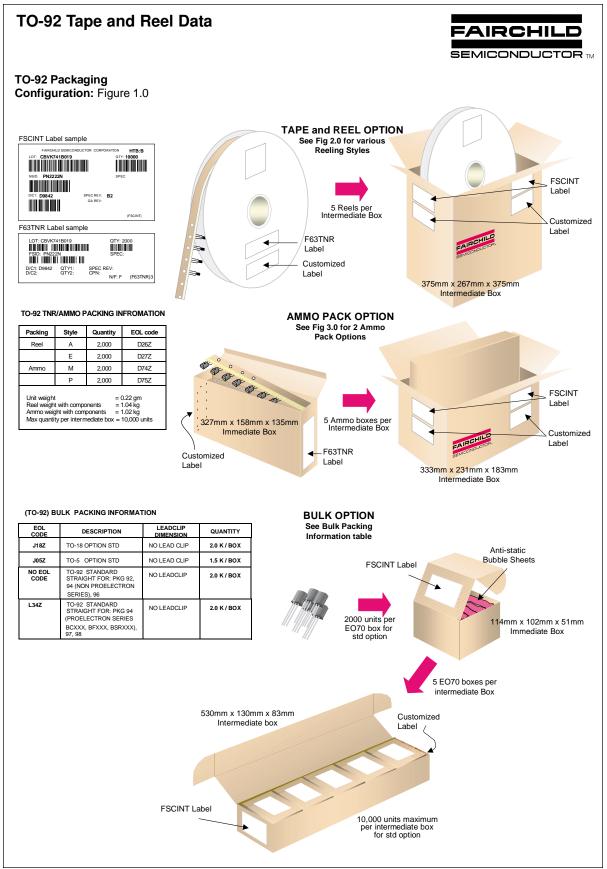
Symbol	Characteristic	Мах	Units
		PN4249	
P _D	Total Device Dissipation	625	mW
	Derate above 25°C	5.0	mW/°C
R _{θJC}	Thermal Resistance, Junction to Case	83.3	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	°C/W

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PNP General Purpose Amplif

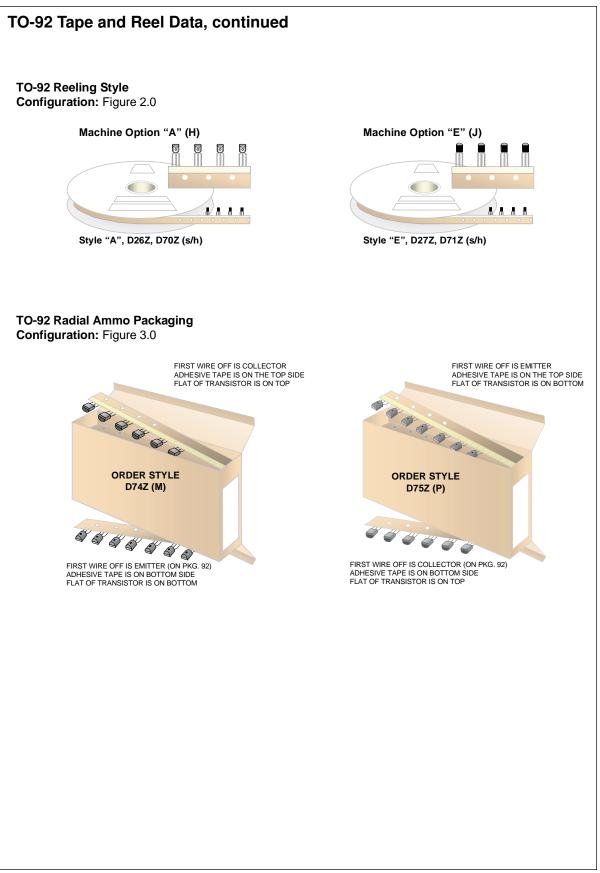
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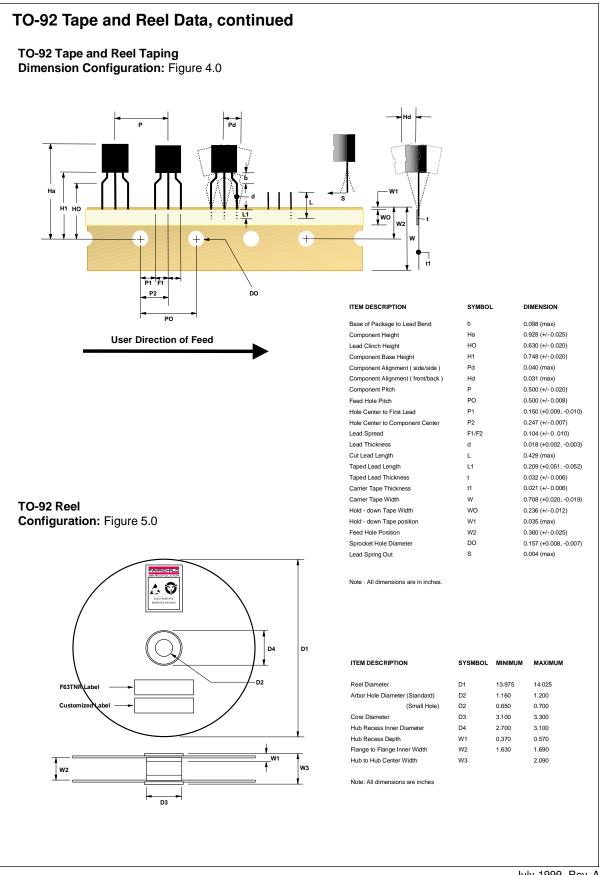
Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHA	RACTERISTICS				
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage*	$I_{\rm C} = 5.0 \text{ mA}, I_{\rm B} = 0$	60		V
V _{(BR)CES}	Collector-Emitter Breakdown Voltage*	$I_{\rm C} = 10 \ \mu A, \ I_{\rm B} = 0$	60		V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	$I_{C} = 10 \ \mu A, \ I_{E} = 0$	60		V
$V_{(\text{BR})\text{EBO}}$	Emitter-Base Breakdown Voltage	$I_E = 10 \ \mu A, \ I_C = 0$	5.0		V
I _{CBO}	Collector-Cutoff Current	$V_{CB} = 40 \text{ V}, I_E = 0$		10	nA
I _{EBO}	Emitter-Cutoff Current	$V_{EB} = 3.0 \text{ V}, I_C = 0$		20	nA
	RACTERISTICS* DC Current Gain	Vce = 5.0 V, Ic = 100 μA	100	300	
h _{FE}		$V_{CE} = 5.0 \text{ V}, \text{ I}_{C} = 100 \ \mu\text{A}$ Ic = 10 mA, I _B = 0.5 mA	100	300 0.25	V
	DC Current Gain		100		V
h _{FE} V _{CE(sat)}	DC Current Gain		100		V
h _{FE} V _{CE(sat)} SMALL S	DC Current Gain Collector-Emitter Saturation Voltage		100		V PF
h _{FE} V _{CE(sat)} SMALL S Cob	DC Current Gain Collector-Emitter Saturation Voltage	I _C = 10 mA, I _B = 0.5 mA	2.5	0.25	
h _{FE} V _{CE(sat)} SMALL S Cob	DC Current Gain Collector-Emitter Saturation Voltage IGNAL CHARACTERISTICS Output Capacitance	$I_{C} = 10 \text{ mA}, I_{B} = 0.5 \text{ mA}$ $V_{CB} = 5.0 \text{ V}, f = 1.0 \text{ MHz}$		0.25 6.0	pF
h _{FE} V _{CE(sat)} SMALL S C _{ob} h _{ie}	DC Current Gain Collector-Emitter Saturation Voltage IGNAL CHARACTERISTICS Output Capacitance Input Impedance	Ic = 10 mA, I _B = 0.5 mA V _{CB} = 5.0 V, f = 1.0 MHz V _{CE} = 5.0 V, I _C = 1.0 mA,	2.5	0.25 6.0 17	pF kΩ
h _{FE} V _{CE(sat)} SMALL S Cob h _{ie} hoe	DC Current Gain Collector-Emitter Saturation Voltage IGNAL CHARACTERISTICS Output Capacitance Input Impedance Output Admittance	Ic = 10 mA, I _B = 0.5 mA V _{CB} = 5.0 V, f = 1.0 MHz V _{CE} = 5.0 V, I _C = 1.0 mA,	2.5	6.0 17 40	pF kΩ μmhos



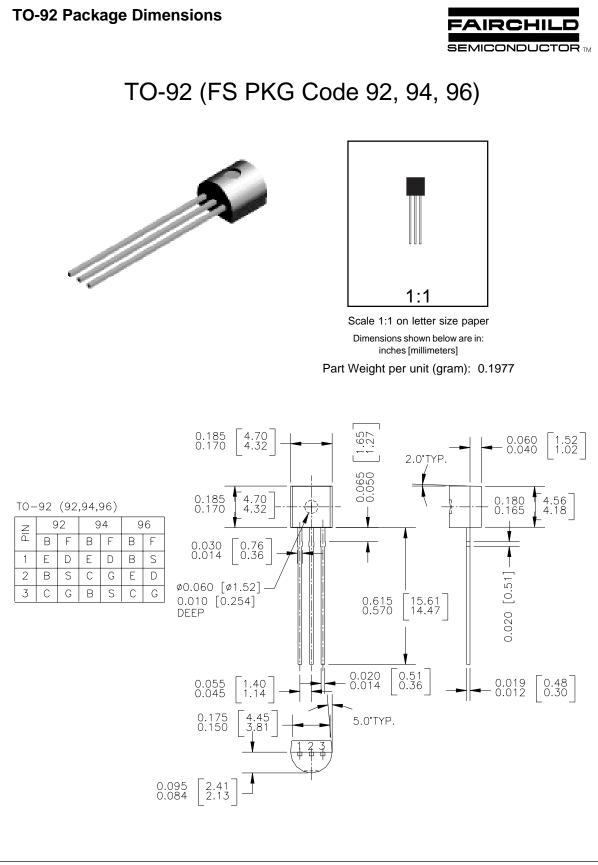
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